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List of Symbols and Abbreviations

α	Absorption coefficient
λ	Wavelength
T_C	Curie temperature
$\tan\delta$	Loss tangent (Dielectric loss)
ε'	Real part of the permittivity
ε''	Imaginary part of the permittivity
d_{33}	Piezoelectric charge coefficient measured along poling direction
E	Electric field
E_a	Activation energy
E_c	Coercive field
E_g	Optical band gap
γ	Diffusivity constant
Ω	Resistance
θ	Theta (degrees)
$\chi 2$	Chi square (Goodness of Fit)
k_B	Boltzmann constant
T	Temperature
T_m	Transition Temperature at the maxima of temperature dependent dielectric constant plot
T_{VF}	Vogel Fulcher temperature

τ	Relaxation time
VFT	Vogel Fulcher Tammann
XRD	X-ray Diffraction
FTIR	Fourier Transform Infrared
Vis	Visible light
UV	Ultraviolet radiation
DRS	Diffuse Reflectance Spectroscopy
SEM	Scanning Electron Microscope
EDS	Energy Dispersive X-ray Spectroscopy
XPS	X-ray Photoemission Spectroscopy
PUND	Positive Up Negative Down
PL	Photo Luminescence
MPB	Morphotropic Phase Boundary
FE	Ferroelectric
DC	Direct Current
PZT	Lead Zirconate, $PbZr_xTi_{1-x}O_3$
BFO	Bismuth Ferrite, $BiFeO_3$
BT	Barium Titanate, $BaTiO_3$
BF-BT	Bismuth Ferrite-Barium Titanate, $BiFeO_3$ -$BaTiO_3$
KNN	Potassium Sodium Niobate, $K_{0.5}Na_{0.5}NbO_3$
BNT	Bismuth Sodium Titanate, $Bi_{0.5}Na_{0.5}TiO_3$
BIT	Bismuth Titanate, $Bi_4Ti_3O_{12}$
PNR	Polar Nano Region
ε	Permittivity

P_s	Saturated Polarization
P_r	Remnant Polarization
E_c	Coercive Electric Field